



AF/2814
IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Tadashi OSHIMA**

Group Art Unit: **2814**

Serial No.: **09/996,758**

Examiner: **Hoai V. Pham**

Filed: **November 30, 2001**

Confirmation No.: **4892**

For: **SEMICONDUCTOR DEVICE WITH TWO TYPES
OF FET's HAVING DIFFERENT GATE LENGTHS
AND ITS MANUFACTURE METHOD**

Attorney Docket No.: **011318**

Customer Number: **38834**

RESPONSE AFTER FINAL

BOX: AF
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

August 27, 2004

Sir:

In response to the Office Action dated June 3, 2004, please amend the above-identified application as follows and consider the following remarks.

Amendments to the Claims are reflected in the listing of claims that begins on page 2 of this paper.

Remarks/Arguments begin on page 8 of this paper.